NSN 5961-01-177-4725

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View Online at https://aerobasegroup.com/nsn/5961-01-177-4725 **Inclosure Material:** Metal **Overall Length:** 0.290 inches **Overall Height:** 0.490 inches **Overall Width:** 0.160 inches Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-89 **Component Name And Quantity:** 2 transistor **Mounting Method:** Press fit **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 45.0 collector to base voltage, dc all transistor and 30.0 collector to emitter voltage, dc all transistor and 5.0 emitter to base voltage, dc all transistor **Voltage Tolerance In Percent:** -5.0/+5.0 all transistor **Current Rating Per Characteristic:** 30.00 milliamperes source cutoff current all transistor **Power Rating Per Characteristic:** 1.4 watts small-signal input power, common-collector preset all transistor **Capacitance Rating In Picofarads:** 8.0 all transistor **Transfer Ratio:** 1.0 static forward current transfer ratio, common-emitter all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius ambient air **Special Features:** All transistor junction pattern arrangement: npn **Terminal Type And Quantity:** 9 uninsulated wire lead Shelf Life: N/a **Unit Of Measure:**

Demilitarization:

Yes - demil/mli

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